Page 13,   line 8, change "voltage-lowing" to --voltage-lowering--.

Page 16,   line 17, change "NOMOS" to --NMOS--.

Page 20,   line 5, change "a" to --the--;

                line 10, change "terminal." to --terminal).--;

                line 27, change "voltage-lowing" to --voltage-lowering--.

Page 21,   line 19, after "drain" (second occurrence) insert --of--;

                line 25, after "between" insert --resistors R1 and R2--.

Page 30,   after "buffer" insert --circuit--.

Page 31,   after "decoder" insert --60--.

Page 32,   line 3, delete "is";

                line 4, change "act" to --acts--.

IN THE CLAIMS:

Please amend the claims as follows:

1.   (Amended)   A semiconductor integrated circuit device comprising:

a semiconductor substrate on which a plurality of transistors including gate insulation films

of different thicknesses are formed; and

an input/output terminal formed on the semiconductor substrate, wherein a transistor

connected directly to the input/output terminal [being] is one of the transistors other than a

transistor having the thinnest gate insulation film.

Claim 2,   line 4, before "a" insert --wherein--;

                line 5, change "being" to --is--.